

ST1802FH

HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

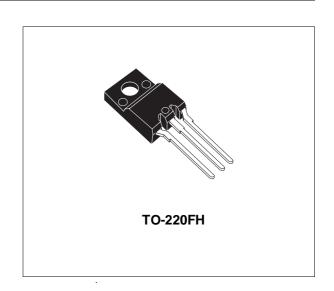
- NEW Fully Plastic TO-220 for HIGH VOLTAGE APPLICATIONS
- NEW SERIES, ENHANCED PERFORMANCE
- EASY MOUNTING
- HIGH VOLTAGE CAPABILITY (> 1500 V)
- HIGH SWITCHING SPEED
- TIGTHER hfe CONTROL
- IMPROVED RUGGEDNESS
- FULLY MOLDED INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- CREEPAGE DISTANCE PATH > 4 mm

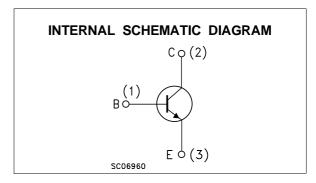


 HORIZONTAL DEFLECTION FOR COLOR TVs UP TO 21 INCHES



The device is manufactured using Diffused Collector Technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage (I _E = 0)	1500	V
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	600	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)	7	V
Ic	Collector Current	10	Α
I _{CM}	Collector Peak Current (tp < 5 ms)	15	Α
I _B	Base Current	4	Α
P _{tot}	Total Dissipation at T _c = 25 °C	40	W
V _{isol}	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

December 2002 1/6

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THERMAL DATA

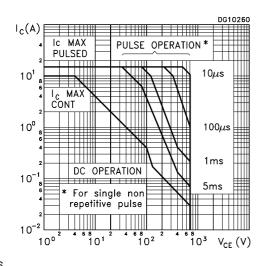
R _{thj-case}	Thermal Resistance Junction-case	Max	3.125	°C/W
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ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

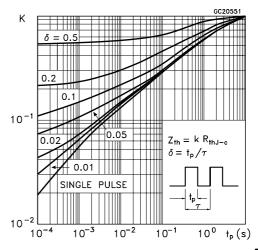
Symbol	Parameter	Test	Conditions	Min.	Тур.	Max.	Unit
I _{CES}	Collector Cut-off Current (V _{BE} = 0)	V _{CE} = 1500 V V _{CE} = 1500 V	T _C = 125 °C			1 2	mA mA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 7 V				1	mA
V _{CEO(sus)*}	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	L = 25 mH	600			V
V _{CE(sat)*}	Collector-Emitter Saturation Voltage	I _C = 4 A I _C = 4 A	$I_B = 0.8 A$ $I_B = 1.2 A$			5 1.5	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage	I _C = 4.5 A	I _B = 1 A			1.2	V
h _{FE} *	DC Current Gain	I _C = 1 A I _C = 5 A I _C = 5 A	V _{CE} = 5 V V _{CE} = 1 V V _{CE} = 5 V	4	25 4.5	9	
t _s	INDUCTIVE LOAD Storage Time Fall Time	I _C = 4 A L _B = 5 μH f = 16 KHz	$I_{Bon(END)} = 1 A$ $V_{BB(off)} = -2.5 V$ (see figure 1)		2.6 0.2	4 0.6	μs μs

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

Safe Operating Area

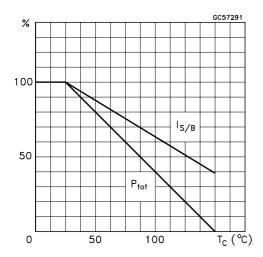


Thermal Impedance

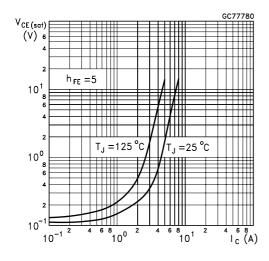


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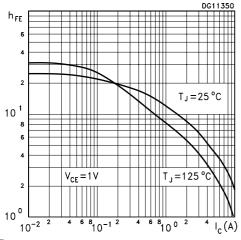
Derating Curve



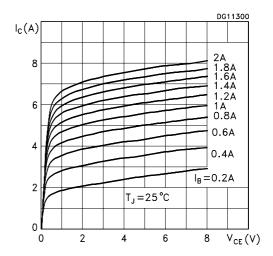
Collector Emitter Saturation Voltage



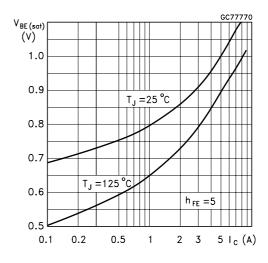
DC Current Gain



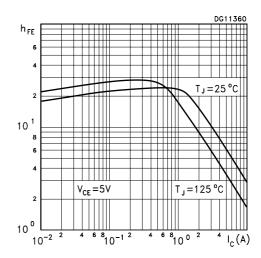
Output Characteristics



Base Emitter Saturation Voltage

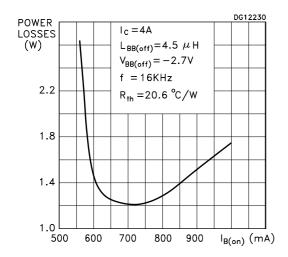


DC Current Gain

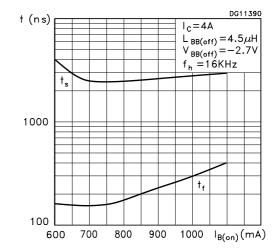


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Power Losses At 16 KHz



Switching Time Inductive Load



Reverse Biased SOA

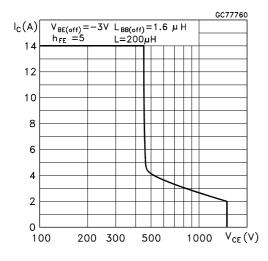
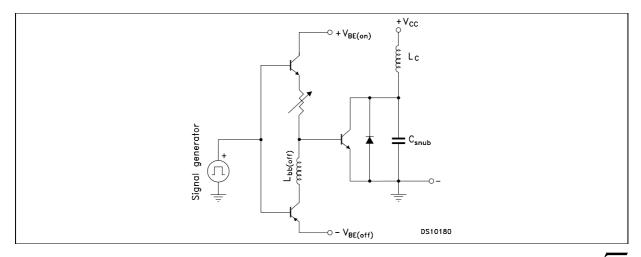


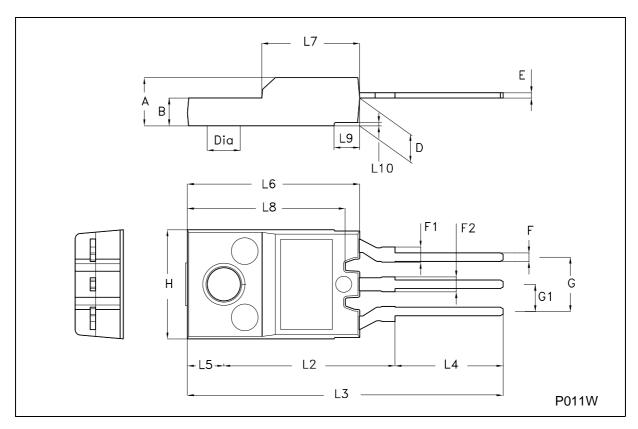
Figure 1: Inductive Load Switching Test Circuit.



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TO-220FH (Fully plastic High voltage) MECHANICAL DATA

DIM.	mm		inch			
DIWI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
В	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.3		1.8	0.051		0.070
F2	1.3		1.8	0.051		0.070
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
Н	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L5		3.4			0.134	
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
L8	14.5		15	0.570		0.590
L9		2.4			0.094	



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